



Attorney ref: US010292

PATENT

7/B w/ ATTACHMENT
1/6/03
Muller
TECHNOLOGY CENTER 2800
2823
RECEIVED
DEC 31 2002

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of: DEV ALOK

U.S. Serial No.: 09/894,084 ✓

Group Art Unit: 2823

Filed: June 28, 2001 ✓

Examiner: SUK SAN FOONG

Title: SILICON CARBIDE SCHOTTKY BARRIER DIODE AND METHOD OF MAKING

AMENDMENT

This amendment is filed in response to the Office Action dated October 2, 2002. There are 17 claims pending in the application. Claims 9 – 17 were withdrawn from consideration in response to a restriction requirement. Claims 1 – 8 stand rejected.

IN THE SPECIFICATION:

Please amend the paragraph beginning in the middle of page 3 to read as follows:

B¹
A Schottky barrier diode is illustrated in Figure 1 that is formed according to the process of prior filed patent application No. 09/700,627, incorporated herein by reference. Ohmic contact layer 18, for example having metal contacts, and preferably formed of titanium, and Schottky rectifying contact 14 are deposited on and bonded to a SiC wafer 10. An ion implanted edge termination region 16 is created in SiC wafer 10 adjacent the edges of Schottky contact 14, preferably using an inert gas ion, for